VS-30EPU12LHN3

Vishay Semiconductors

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Ultrafast Rectifier, 30 A FRED Pt®



PRODUCT SUMMARY								
Package	TO-247AD 2L							
I _{F(AV)}	30 A							
V _R	1200 V							
V _F at I _F at 125 °C	2.05 V							
t _{rr}	49 ns							
T _J max.	175 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and soft recovery
- Optimized forward voltage drop
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Rugged design
- Good thermal performance
- AEC-Q101 qualified available
- Meets JESD 201 class 1 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, recovery time, and soft recovery. Polyimide passivated, planar structure, and the platinum doped life time control guarantee, ruggedness, reliability characteristics, and solid value proposition for efficiency and thermal performance.

These devices are intended for use in boost stage in the AC/DC section of SMPS, high frequency output rectification of battery charger, inverters for solar inverters, or as freewheeling diodes in motor drive.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		1200	V						
Average rectified forward current	I _{F(AV)}	T _C = 135 °C, D = 0.50	30							
Non-repetitive peak surge current	I _{FSM}	T_{C} = 25 °C, t_{p} = 10 ms, sine wave	300	A						
Repetitive peak forward current	I _{FRM}		60							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 500 μA	1200	-	-				
Forward voltage	V _F	I _F = 30 A	-	2.15	2.68	V			
i orward voltage		$I_F = 30 \text{ A}, T_J = 125 \text{ °C}$	-	2.05	2.45				
Poveros loskago surrent	I	$V_{R} = V_{R}$ rated	-	-	145				
Reverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	320	μΑ			
Junction capacitance	CT	V _R = 200 V	-	29	-	pF			
Series inductance	Ls	Measured to lead 5 mm from package body	-	8	-	nH			

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 10$	-	49	-					
Reverse recovery time	t _{rr}	T _J = 25 °C		-	220	-	ns A			
		T _J = 125 °C		-	356	-				
Doold recovery ourrent	1	$T_J = 25 \ ^\circ C$	$I_{\rm F} = 30 {\rm A}$	-	8.2	-				
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 100 A/µs V _B = 390 V	-	13.3	-				
	0	T _J = 25 °C		-	900	-	nC			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	2388	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction to case	R _{thJC}		-	0.35	0.42					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	30	33	°C/W				
Thermal resistance, case to heat sink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.25	0.4					
Weight			-	0.2	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style: TO-247AD 2L		30EPI	J12LH					

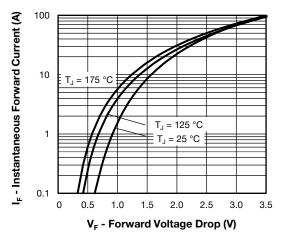


Fig. 1 - Typical Forward Voltage Drop Characteristics

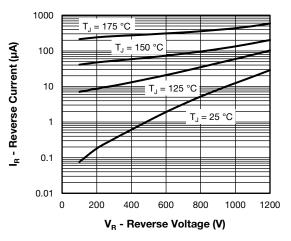


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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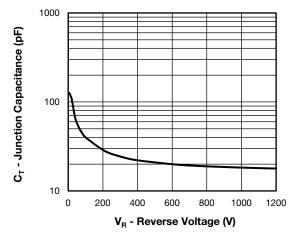


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

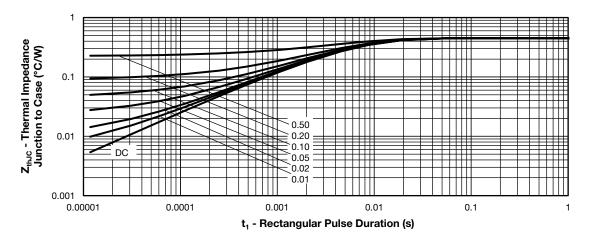


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

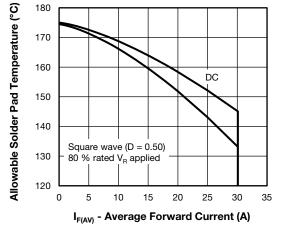


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

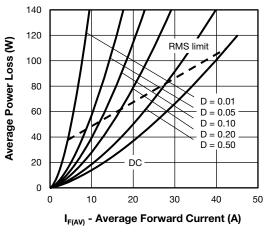


Fig. 6 - Forward Power Loss Characteristics

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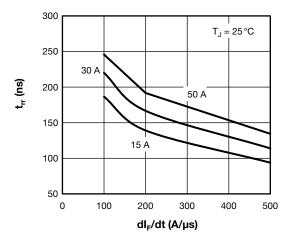


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

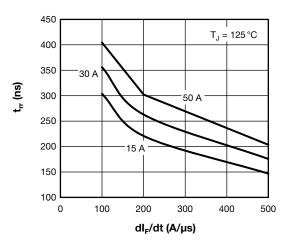


Fig. 8 - Typical Reverse Recovery Time vs. dI_F/dt

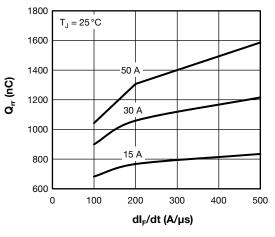


Fig. 9 - Typical Stored Charge vs. dl_F/dt

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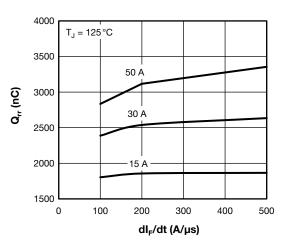


Fig. 10 - Typical Stored Charge vs. dl_F/dt

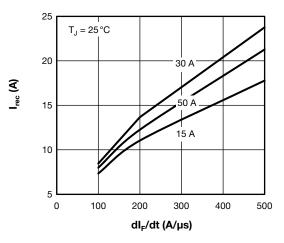


Fig. 11 - Typical Reverse Current vs. dl_F/dt

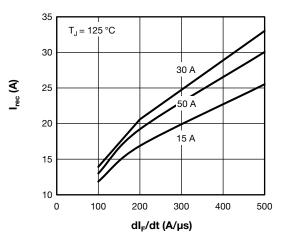


Fig. 12 - Typical Reverse Current vs. dl_F/dt

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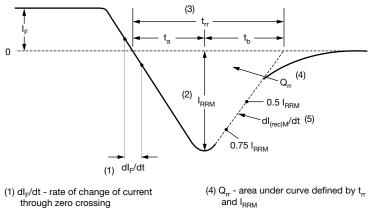
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(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\mathrm{I}_{\mathrm{RRM}}$ and 0.50 $\mathrm{I}_{\mathrm{RRM}}$ extrapolated to zero current.

and I_{RRM}

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 13 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device code	VS-	30	Е	Р	U	12	L	н	N3		
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)		
	1 - Vishay Semiconductors product										
	2 - Current rating (30 = 30 A)										
	3 -	3 - Circuit configuration: E = single diode									
	4 -	P =	TO-247	' packag	je						
	5 - Process type: U = ultrafast recovery										
	6 -	Volt	age rati	ng (12 =	= 1200 \	/)					
	7 - L = long lead										
	8 - H = AEC-Q101 qualified										
	9 - Environmental digit:										
		N3	= haloge	en-free,	RoHS-c	complia	nt, and t	totally le	ad (Pb)		

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-30EPU12LHN3	25	500	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95536					
Part marking information	www.vishay.com/doc?95648					

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TO-247AD 2L

DIMENSIONS in millimeters and inches



Section C - C, D - D

(b. b2)

(4)

/	\square
	C C
Vie	<u>w B</u>

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			Е	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102			E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098			е	5.46	BSC	0.215	BSC	
b	0.99	1.40	0.039	0.055			ØК	0.2	254	0.0)10	
b1	0.99	1.35	0.039	0.053			L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	
D2	0.51	1.35	0.020	0.053								

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

⁽²⁾ Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

(7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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